

## ABSTRACT

The present invention relates to low dielectric materials essential for a semiconductor having high density and high performance of the next generation,  
5 particularly to a process for preparing a porous interlayer insulating film having low dielectric constant containing pores with a size of a few nanometers or less.

The present invention provides a process for preparing a porous wiring interlayer insulating film having very low dielectric constant for a semiconductor device comprising the steps of a) preparing a mixed complex of pore-forming organic molecules and a matrix resin, b) coating the mixed complex on a substrate, and c) heating the mixed complex to remove the organic molecules therefrom, thereby forming pores inside the complex.  
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The porous wiring interlayer insulating film having very low dielectric constant prepared according to the process of the present invention has reduced phase-separation, excellent processibility, isotropic structure and very small pores with a size of a few nanometers or less.  
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